

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ATTORNEY DOCKET NO.: AGX-37-RCE-CPA

In re Application of: Shooshtarian, et al.

Group Art Unit: 2823

Serial No.: 09/527,873

Examiner: Hsein-Ming Lee

Filed: March 17, 2000

Our Account No.: 04-1403

Confirmation No.: 4182

Title: Localized Heating and Cooling of Substrates

Commissioner for Patents  
U.S. Patent and Trademark Office  
Washington, DC 20231



RECEIVED  
OCT 25 2002  
TECHNOLOGY CENTER-2800

**AMENDMENT**

This is a response/amendment/letter in the above-identified application and includes the herewith attachment of same date and subject which is incorporated hereinto by reference and the signature below is to be treated as the signature to the attachment in absence of a signature thereto.

Fee requirements (if any) have been calculated as shown below:

	Claims remaining after amendment		Highest number previously paid for		Present Extra		Additional Fee
Total Effective Claims	19	minus	41	=	0	x \$18 =	\$ 0.00
Independent Claims	3	minus	4	=	0	x \$84 =	\$ 0.00
If amendment enters proper multiple dependent claim(s) into this application for first time, add \$270.00 (per application)							\$
Since Official Action set an original due date of 09/19/02, PETITION is hereby made for an extension to cover the date this response is filed for which the requisite fee is enclosed (1 month \$110; 2 months \$400; 3 months \$920; 4 months \$1440)							\$ 110.00
If Terminal Disclaimer enclosed, add Rule 20(d) Official Fee (\$110.00)							\$
<b>SUBTOTAL:</b>							\$ 110.00
If "small entity" verified statement filed [ ] previously, [ ] herewith, enter one-half (1/2) of subtotal and subtract							\$
<b>TOTAL:</b>							\$ 110.00
Other: Information Disclosure Statement List w/3 Cited References							\$ 180.00
<b>TOTAL FEE ENCLOSED:</b>							\$ 290.00

The Commissioner is hereby authorized to charge any fee specifically authorized hereafter, or any fees in addition to the fee(s) filed, or asserted to be filed, or which should have been filed herewith or concerning any paper filed hereafter, and which may be required under Rules 16-18 (deficiency only) now or hereafter relative to this application and the resulting official document under Rule 20, or credit any overpayment, to our Account No. shown in the heading hereof for which purpose a duplicate copy of this sheet is attached. This statement does not authorize charge of the issue fee in this case.

ADDRESS:  
Post Office Box 1449  
Greenville, South Carolina 29602  
Phone: 864-271-1592  
Facsimile: 864-233-7342

**DORITY & MANNING**  
**ATTORNEYS AT LAW, P.A.**

By Atty: Jason W. Johnston Reg. No.: 45,675

Signature:

I hereby certify that this correspondence and any referenced attachment and fee are being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, U.S. Patent and Trademark Office, Washington, DC 20231, on October 17, 2002.

Lyan Watkins  
(Typed or printed name of person mailing paper or fee)  
(Signature of person mailing paper or fee)



#22 / AMOT  
D  
10/29/02  
✓8

**PATENT**  
**ATTORNEY DOCKET NO.: AGX-37-RCE-CPA**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application	)	
Shooshtarian, et al.	)	Examiner: Hsein-Ming Lee
	)	
Serial No.: 09/527,873	)	Art Unit: 2823
	)	
Filed: March 17, 2000	)	Dept. Acct. No.: 04-1403
	)	
Title: Localized Heating and	)	
Cooling of Substrates	)	

RECEIVED  
OCT 25 2002  
TECHNOLOGY CENTER 2800

Commissioner for Patents  
Washington, D.C. 20231

**AMENDMENT**

Dear Sir:

In response to the Office Action dated June 19, 2002, please amend the above-captioned applications as follows:

**IN THE CLAIMS:**

Please add the following claims:

Sub E8  
42. A method as defined in claim 1, wherein said gas used to selectively control the temperature of at least one of said localized regions is supplied by a device located below said semiconductor wafer.

D  
43. A method as defined in claim 42, wherein said device is a reflective device through which a plurality of gas outlets extend.

Sub E9  
44. A method as defined in claim 1, wherein said gas used to selectively control the temperature of at least one of said localized regions is supplied by a device located above said semiconductor wafer.